

Notice of References Cited

Application/Control No.

10/599,106

Applicant(s)/Patent Under
Reexamination
ZHU ET AL.

Examiner

ALLAN OLSEN

Art Unit

1716

Page 1 of 1

U.S. PATENT DOCUMENTS

| * | | Document Number Country Code-Number-Kind Code | Date MM-YYYY | Name | Classification |
|---|---|--|-----------------|------------------|----------------|
| * | A | US-4,393,127 A | 07-1983 | Greschner et al. | 430/5 |
| * | B | US-6,764,898 B1 | 07-2004 | En et al. | 438/240 |
| * | C | US-2007/0117396 A1 | 05-2007 | Wu et al. | 438/710 |
| * | D | US-2009/0321644 A1 | 12-2009 | Vogt et al. | 250/338.4 |
| * | E | US-2011/0006208 A1 | 01-2011 | Freitag et al. | 250/307 |
| | F | US- | | | |
| | G | US- | | | |
| | H | US- | | | |
| | I | US- | | | |
| | J | US- | | | |
| | K | US- | | | |
| | L | US- | | | |
| | M | US- | | | |

FOREIGN PATENT DOCUMENTS

| * | | Document Number Country Code-Number-Kind Code | Date MM-YYYY | Country | Name | Classification |
|---|---|--|-----------------|---------|------|----------------|
| | N | | | | | |
| | O | | | | | |
| | P | | | | | |
| | Q | | | | | |
| | R | | | | | |
| | S | | | | | |
| | T | | | | | |

NON-PATENT DOCUMENTS

| * | | Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages) | | | | |
|---|---|---|--|--|--|--|
| * | U | Winters, H. F.; Coburn, J. W.; The etching of silicon with XeF ₂ vapor Applied Physics Letters, Volume 34, Issue 1, id. 70 (1979). | | | | |
| | V | XeF ₂ Etching of Silicon Characteristics: dry, isotropic, vapor www-inst.eecs.berkeley.edu/~ee143/fa10/lab/XeF2_tutorial.pdf | | | | |
| * | W | Brazzle, J.D.; Dokmeci, M.R.; Mastrangelo, C.H.; Modeling and characterization of sacrificial polysilicon etching using vapor-phase xenon difluoride, 17th IEEE International Conference on Micro Electro Mechanical Systems (MEMS), 2004, pages 737-740. | | | | |
| | X | | | | | |

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.06(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.